

5 an isolation region provided in a strip-shape and having a peak impurity concentration at
 a prescribed depth position from the main surface of said semiconductor substrate;
 a connection hole provided piercing through said element isolating region;
 an anti-HF (hydrofluoric acid) side wall film not etched by hydrofluoric acid, provided to
 cover a side wall of said connection hole at least near a lower end of said connection hole;
 10 an interconnection layer provided to fill an inner portion of said connection hole; and
 an impurity region provided in said semiconductor substrate extending from the lower
 end of said connection hole to said isolation region, wherein said impurity region comprises a
first impurity region portion provided to connect said interconnection layer to said isolation
region, and a second impurity region portion provided near the lower end of said connection hole
 15 and connected to said interconnection layer.

REMARKS

Claims 1 through 7 are pending in this application. Claims 5 through 7 stand withdrawn from consideration. In response to final Office Action dated December 9, 1999, it is proposed above that claim 3 be cancelled and that independent claim 1 be amended to substantially include the subject matter of claim 3. It is believed that a cursory review of the proposed Amendment, in light of the following explanation, would lead to a conclusion that the application is in condition for allowance. A request for one month extension of the period for response and appropriate fee charge authorization accompany this submission. Entry of the Amendment is respectfully solicited, even if only for purpose of Appeal, if an Appeal should later be taken.

Claim 1, amended as proposed herein, recites a structure such as illustrated in Fig. 1, wherein first impurity region portion 52 is formed to connect interconnection layer 13 and